

IN THE CLAIMS:

Please cancel claims 1 and 2 in their entirety without prejudice nor disclaimer of the subject matter set forth therein.

Please amend claims 3, 5 and 9 as follows:

1.-2. (Canceled)

3. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component by using a plasma derived from an etching gas containing a H<sub>2</sub> gas, a N<sub>2</sub> gas, and a F<sub>2</sub> gas, but no component which oxidizes the organic component O<sub>2</sub>-gas.

4. (Original) The etching method of claim 3, wherein said etching gas contains an inert gas.

5. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component by using a plasma derived from an etching gas containing a H<sub>2</sub> gas and a nitrogen trifluoride gas, but no component which oxidizes the organic component O<sub>2</sub>-gas.

6. (Original) The etching method of claim 5, wherein said etching gas contains an inert gas.

7. (Previously Presented) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component by using a plasma derived from an etching gas containing a N<sub>2</sub> gas and a hydrogen fluoride gas.

8. (Original) The etching method of claim 7, wherein said etching gas

contains an inert gas.

9. (Currently Amended) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component by using a plasma derived from an etching gas containing a N<sub>2</sub> gas and a fluorinated hydrocarbon gas, but no component which oxidizes the organic component O<sub>2</sub>-gas.

10. (Original) The etching method of claim 9, wherein said etching gas contains an inert gas.

11. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon dioxide gas and a fluorine gas as main constituents.

12. (Withdrawn) The etching method of claim 11, wherein said etching gas contains an inert gas.

13. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon dioxide gas and a fluorinated hydrocarbon gas as main constituents.

14. (Withdrawn) The etching method of claim 13, wherein said etching gas contains an inert gas.

15. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-

inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon monoxide gas and a fluorinated gas as main constituents.

16. (Withdrawn) The etching method of claim 15, wherein said etching gas contains an inert gas.

17. (Withdrawn) An etching method comprising the step of performing anisotropic etching with respect to an interlayer insulating film composed of an organic-inorganic hybrid film containing an organic component and a silica component as main constituents by using a plasma derived from an etching gas containing a carbon monoxide gas and a fluorinated gas as main constituents.

18. (Withdrawn) The etching method of claim 17, wherein said etching gas contains an inert gas.